

**AMENDMENTS TO THE SPECIFICATION**

Please replace current paragraphs [0005] and [0114] of the specification with the following new paragraphs [0005] and [0114] as follows.

[0005] Each power module base plate 41 is constituted so as to include an AlN/Al joint material 45 and a semiconductor chip 35. The AlN/Al joint material 45 is constituted by a circuit layer 43 made of aluminum being laminated on the first side of an insulated base plate 42 made of AlN (hereinbelow, referred to as an AlN base plate 42), and a metal layer 44 made of aluminum being laminated on the second side of the AlN base plate 42. The semiconductor chip 35 is mounted on the circuit layer 43 via solder 34. As the metal layer ~~43~~ 44 or the circuit layer ~~[[44]]~~ 43, 4N-Al (aluminum with purity greater than 99.99%) may be used to constitute the AlN/Al joint material.

[0114] The second evaluation was an observation of a strain occurring region ~~the same as in the first evaluation~~. In the second evaluation, ~~TEM observation (bright field) imaging of the ceramic crystal grain on the interface was performed~~. ~~The~~ the strain of the crystal grain was defined as an inhomogeneous strain analysis value obtained from a crystallite size and a lattice inhomogeneous strain measured by X-ray diffraction, and the damage is expressed as the strain. In the TEM observation, the thickness of the sample was set so that dislocation does not disappear. The results of these experiments are shown in the Table 1 below.